

METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE

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ABSTRACT OF THE DISCLOSURE

10       The resist film is provided on the surface of the  
substrate having electrodes, and openings are provided in  
the resist film at positions of the electrodes on the  
substrate. The first metal is supplied into the  
openings. The first metal is then heated to melt and  
coagulate it. The second metal is then supplied into the  
openings on the first metal. The first metal and the  
15       second metal are heated to melt and coagulate them. The  
resist film is finally removed. By this method,  
excellent solder bumps can be formed on the substrate  
without remnants of the resist film being left on the  
substrate.